

### **Amendments to the Specification**

***Please replace the abstract with the following amended abstract:***

In a method of manufacturing a nonvolatile semiconductor storage device, an element isolation region ~~(12 in Fig. 1)~~ is formed in a semiconductor substrate ~~[(11)]~~, a tunnel oxide film ~~[(13)]~~ and a polysilicon layer ~~to become a floating gate (14) later~~ are successively formed on the ~~resulting~~ semiconductor substrate, and nitrogen ions are thereafter implanted into the front surface of the polysilicon layer so as to stay in the only this front surface only. The polysilicon layer is patterned to form ~~[(the)]~~ a floating gate ~~[(14)]~~, ~~and this floating gate (14) which is then thermally oxidized to form an inter-gate insulating film [(15)]~~. Since ~~[(the)]~~ thermal oxidation is suppressed by ~~[(the)]~~ nitrogen ions, the inter-gate insulating film ~~(15) can be made~~ is thicker at the side surfaces of the floating gate ~~[(14)]~~ than at the front surface thereof. Thus, the The inter-gate insulating film ~~[(15)]~~ at the edge ~~[(part)]~~ of the floating gate ~~[(14)]~~ can be formed as designed, so that the ~~nonvolatile semiconductor~~ storage device is free from bad influence ~~on its~~ during electrical programming and erasing, and ~~is capable of retaining charges for a long time~~ can retain charge longer.